## SK 80 TAA



# SEMITOP®3

### Thyristor module

#### SK 80 TAA

**Target Data** 

#### **Features**

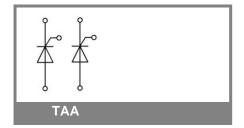
- Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide (DCB)
- Glass passivated thyristor chips
- Up to 1600V reverse voltage
- · High surge currents

### **Typical Applications**

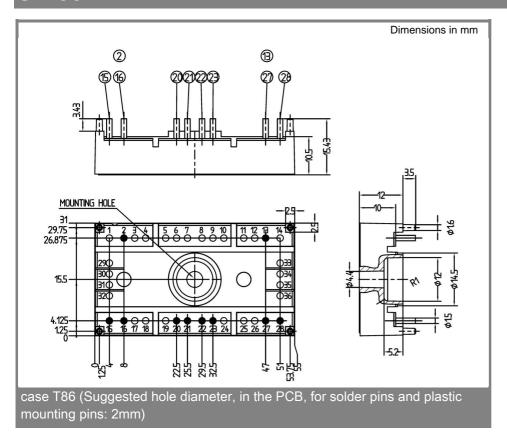
- Motor drives
- Controlled battery chargers

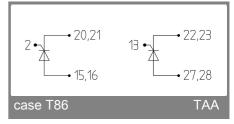
V <sub>RSM</sub> V	V <sub>RRM</sub> , V <sub>DRM</sub>	$I_D = 81 \text{ A (full conduction)}$ $(T_S = 80 ^{\circ}\text{C})$
900	800	SK 80 TAA 08.
1300	1200	SK 80 TAA 12
1700	1600	SK 80 TAA 16

Symbol	Conditions	Values	Units
I <sub>D</sub>	T <sub>s</sub> = 80 °C	81	Α
I <sub>TSM</sub>	T <sub>vi</sub> = 25 °C; 10 ms	2000	Α
	T <sub>vi</sub> = 125 °C; 10 ms	1800	Α
i²t	$T_{vj}$ = 25 °C; half sine wave, 10 ms	20000	A²s
	T <sub>vj</sub> = 25 °C; half sine wave,10 ms	16200	A²s
V <sub>T</sub>	T <sub>vj</sub> = 25 °C; I <sub>T</sub> = 300 A	max. 1,85	V
$V_{T(T0)}$	T <sub>vi</sub> = 125 °C;	max. 0,85	V
r <sub>T</sub>	T <sub>vj</sub> = 125 °C	max. 3,5	mΩ
$I_{DD}$ ; $I_{RD}$	$T_{vj}$ = 125 °C; $V_{DD}$ = $V_{DRM}$ ; $V_{RD}$ = $V_{RRM}$	max. 10	mA
t <sub>gd</sub>	$T_{vj} = 25 \text{ °C; } I_G = 1 \text{ A; } di_G/dt = 1 \text{ A/}\mu\text{s}$	1	μs
t <sub>gr</sub>	$V_D = 0.67 \cdot V_{DRM}$	2	μs
(dv/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C	max. 1000	V/µs
(di/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C; f = 50 60 Hz	max. 50	A/µs
$t_q$	$T_{vj} = 125 ^{\circ}\text{C}; \text{ typ.}$	80	μs
I <sub>H</sub>	$T_{vj} = 25 ^{\circ}\text{C}$ ; typ. / max.	100 / 200	mA
$I_{\underline{L}}$	$T_{vj} = 25  ^{\circ}\text{C};  R_{G} = 33  _{\Omega}$	200 / 500	mA
V <sub>GT</sub>	T <sub>vj</sub> = 25 °C; d.c.	min. 2	V
$I_{GT}$	$T_{vj} = 25  ^{\circ}\text{C}; \text{d.c.}$	min. 100	mA
$V_{GD}$	$T_{vj} = 125 ^{\circ}\text{C}; \text{d.c.}$	max. 0,25	V
$I_{GD}$	T <sub>vj</sub> = 125 °C; d.c.	max. 5	mA
R <sub>th(j-s)</sub>	cont.per thyristor	0,45	K/W
• ,	sin. 180° per thyristor	0,47	K/W
T <sub>solder</sub>	Terminals, 10s	260	°C
T <sub>vi</sub>		-40 <b>+</b> 125	°C
T <sub>stg</sub>		-40 <b>+12</b> 5	°C
V <sub>isol</sub>	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3000 ( 2500 )	V
M <sub>s</sub>	Mounting torque to heatsink	typ. 2,5	Nm
m		30	g
Case	SEMITOP®2	T 86	



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